

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (currently amended) A semiconductor device comprising a field effect transistor formed on a SOI substrate, the semiconductor device characterized in comprising:

a gate region formed on a semiconductor film of the SOI substrate;

source and drain regions each spaced a specified distance from a channel region formed in the semiconductor film below the gate region;

a first extension region ~~formed independently of the source region~~ that extends from the source region to the channel region; and

a second extension region ~~formed independently of the drain region~~ that extends from the drain region to the channel region,

wherein junction depths of the first and second extension regions are ~~formed to be shallower than~~ 50% or less of junction depths of the source region and the drain region.

2. (cancelled)

3. (currently amended) A semiconductor device according to claim 1 ~~or claim 2~~ characterized in operating in a fully depleted operation mode.

4. (original) A semiconductor device according to ~~any one of claim 1 through~~
or claim 3, wherein the SOI substrate is a substrate composed of a glass substrate, a
quartz substrate or another insulation substrate and a semiconductor film formed
thereon.

5-8. (cancelled)

9. (new) A semiconductor device comprising a field effect transistor
characterized in operating in fully depleted operation mode formed on an SOI substrate,
the semiconductor device characterized in comprising:

a gate region formed on a semiconductor film of the SOI substrate;

source and drain regions each spaced a specified distance from a channel
region formed in the semiconductor film below the gate region;

a first extension region that extends from the drain region to the channel
region; and

a second extension region that extends from the drain region to the
channel region,

wherein junction depths of the first and second extension regions are 50%
or less of the junction depth of each of the source region and the drain region.